Zero-Drift, Low Power, CMOS Operational Amplifiers

Features

- Low Offset Voltage: ±7μV (TYP)
- Input Offset Voltage Drift: ±0.08μV/°C
- Gain Bandwidth Product: 350KHz
- Rail-to-Rail Input and Output
- High Gain, CMRR, PSRR: 120dB
- High Slew Rate: 0.16V/us
- Low Noise: 0.9μVp-p (0.01Hz~10Hz)
- Low Power Consumption: 40uA/ Amp
- Overload Recovery Time: 3us
- Low-Supply Voltage: +2.0 V to +5.5 V
- Operating Temperature: -40'C to +125'C

Applications

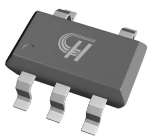
- Handheld Test Equipment
- Medical Instrumentation
- Temperature Measurements
- Battery-Powered Instrumentation
- Transducers
- Electronic Scales

General Description

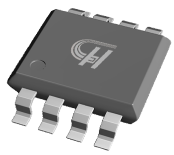
The HCR8541/HCR8542 series of CMOS operational amplifiers use auto-calibration techniques to simultaneously provide very low offset voltage (7μV TYP) and near-zero drift over time and temperature. This family of amplifiers has ultralow noise, offset and power.

This miniature, high-precision operational amplifiers offset high input impedance and rail-to-rail input and rail-to-rail output swing. With gain-bandwidth product of 350KHz and slew rate of 0.16V/μs. Single or dual supplies as low as +2V (±1V) and up to +5.5V (±2.75V) may be used.

The HCR8541/HCR8542 are specified for the extended industrial and automotive temperature range from -40°C to 125°C. The HCR8541 single amplifier is available in SOT-23-5 packages, The RS8542 dual amplifier is available in SOIC-8 (SOP-8) packages.



SOT23-5



SOIC-8(SOP-8)

Figure 1. Package Type of HCR8541/HCR8542

Zero-Drift, Low Power, CMOS Operational Amplifiers

Pin Configuration

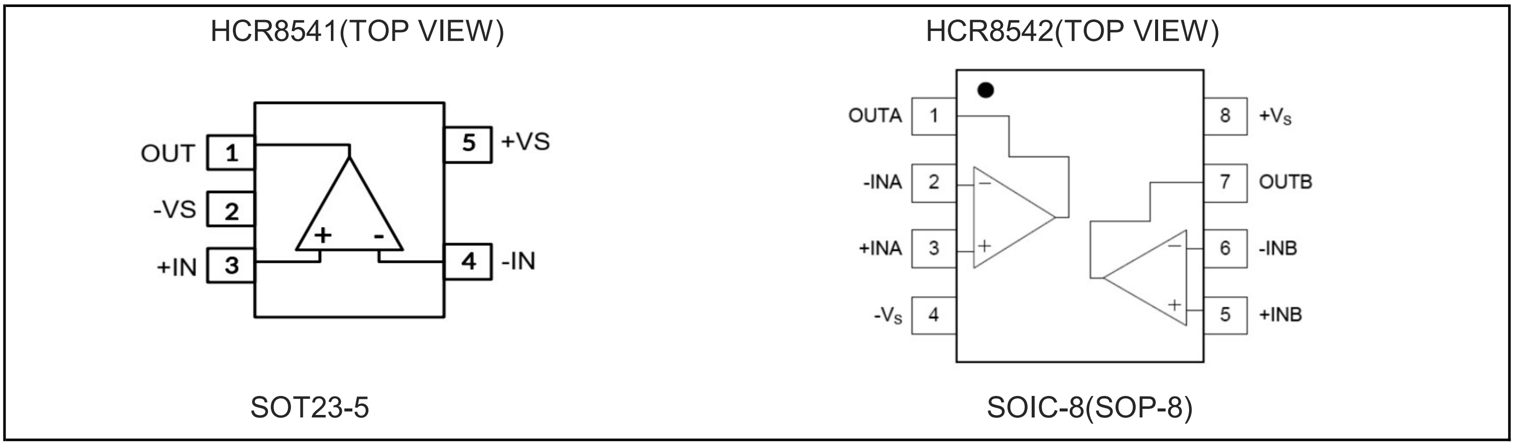
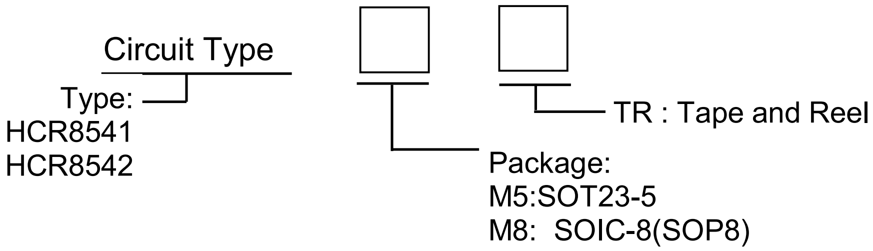


Figure 2. Pin Configuration of HCR8541/HCR8542(Top View)

Pin Function Table

Name	Function
+IN, +INA, +INB	Non-inverting Inputs
-IN, -INA, -INB	Inverting Inputs
+Vs	Positive(highest) Power Supply
-Vs	Negative(lowest) Power Supply
OUT, OUTA, OUTB	Outputs

Ordering Information



Ordering Code

Part Number	Channel	Marking [1]	Op Temp('C)	MSL [2]	Package	Package Qty
HCR8541M5TR	1	8541	-40'C to +125'C	MSL3	SOT23-5	3000pcs/TR
HCR8539M8TR	2	HCR8542xx	-40'C to +125'C	MSL3	SOIC-8 (SOP-8)	4000pcs/TR

note 1: There may be additional marking, which relates to the lot trace code information(data code and vendor code)， the logo or the environmental category on the device.

2: HCRSEMI classify the MSL level with using the common preconditioning setting in our assembly factory conforming to the JEDEC industrial standard J-STD-20F. Please align with HCRSEMI if your end application is quite critical to the preconditioning setting or if you have special requirement.

Absolute Maximum Ratings

Over operating free-air temperature range(unless otherwise noted) (1)

Parameter		Symbol	Min.	Max.	Unit
Supply Voltage, +Vs to -Vs		V+	-	7	V
Signal Input Voltage		VIN	(V-)-0.3	(V+)+0.3	V
Signal Output Voltage		Vout	(V-)-0.3	(V+)+0.3	V
Signal Input Current		IIN	-10	+10	mA
Signal Output Current		IO	-10	+10	mA
Output Short-circuit (3)		-	Continuous		
Thermal Resistance (4) @TA=+25'C	SOT23-5	θJA	-	230	'C/W
	SOIC-8 (SOP8)	θJA	-	110	'C/W
Storage Temperature Range		TSTG	-65 to +150		'C
Operating Temperature Range note 2		TA	-40 to +125		'C
Junction Temperature (5)		TJ	-40 to +150		'C
Lead Temperature (Soldering, 10s)		TLEAD	260		'C
Human Body Model ESD Protection		ESD HBM	±4		KV
Machine Model ESD Protection		ESD MM	±300		V

Note 1. Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

2. Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.5V beyond the supply rails should be current-limited to 10mA or less.

3. Short-circuit to ground, one amplifier per package.

4. The package thermal impedance is calculated in accordance with JESD-51.

5. The maximum power dissipation is a function of TJ(MAX), RθJA, and TA. The maximum allowable power dissipation at any ambient temperature is PD = (T J(MAX) - TA) / RθJA. All numbers apply for packages soldered directly onto a PCB.

Recommended Operating Conditions

Parameter		Symbol	Min.	Max.	Unit
Supply Voltage, +Vs to -Vs	Signal-supply	VIN	2.0	5.5	V
	Dual-supply		±1.0	±2.75	V
Operating Temperature Range		Ta	-40	+125	'C

Electrical Characteristics

(TA=25 `C, Vs=+5V, RL=10KΩ connected to VS/2 and VOUT=VS/2, VCM=VS/2, Unless Otherwise Specified.)

Parameter	Symbol	Conditions	TA	Min	Type	Max	Unit
Offset Voltage							
Input Offset Voltage	VOS	VCM = VS/2	25'C	-30	±7.0	+30	uV
Input Offset Voltage Average Drift	ΔVOS/ΔT	-	25'C	-	±0.08	-	uV/'C
Input Bias Current:							
Input Bias Current:	IB	VCM=VS/2	25'C	-	±330	-	pA
Input Offset Current:	IOS	-	25'C	-	±100	-	pA
Input Voltage Range							
Common-Mode Voltage Range	VCM	-	25'C	(V-)-0.1	-	(V+)+0.1	V
Common Mode Rejection Ratio	CMRR	‘(V-)-0.1V<VCM=(V+)+0.1V	25'C	105	120	-	dB
Differential	-	-	25'C	-	2.5	-	pF
Common-Mode	-	-	25'C	-	5	-	pF
Output Characteristics							
Open-Loop Voltage Gain	AOL	RL=10KΩ, Vo=0.3V to 4.7V	Full	105	130	-	dB
Output Voltage Low from rail	VOL	RL=100KΩ to GND	25'C	-	1	-	mV
		RL=10KΩ to GND	25'C	-	10	20	
Output Voltage High from rail	VOH	RL=100KΩ to V+	25'C	-	1	-	mV
		RL=10KΩ to V+	25'C	-	10	20	
Output Short-Circuit Current	ISHRT	Source	25'C	±20	±30	-	mA
Power Supply							
Operating Voltage Range	Vs		Full	2.0	-	5.5	V
Quiescent Current per Amplifier	IQ		25'C	-	40	60	uA
Power-Supply Rejection Ratio	PSRR	Vs= 2.0V to 5.5V	25'C	95	120	-	dB
Channel Separation, dc	-	-	25'C	-	0.1	-	uV/V
Dynamic Performance							
Gain Bandwidth Product	GBW	-	25'C	-	350	-	KHz
Slew Rate	SR	G=+1	25'C	-	0.16	-	V/uS
Overload Recovery Time	tOR	VIN*Gain>=Vs	25'C	-	3	-	us
Noise Performance							
Input Voltage Noise	enp-p	Vs=5V, f=0.1Hz to 10Hz	25'C	-	0.9	-	uVpp
Input Voltage Noise Density	en	f=1KHz	25'C	-	45	-	nV/ √ Hz

Typical Performance Characteristics.

(TA = +25°C, VS=5V, RL = 10kΩ connected to VS/2, VOUT = VS/2, unless otherwise noted.)

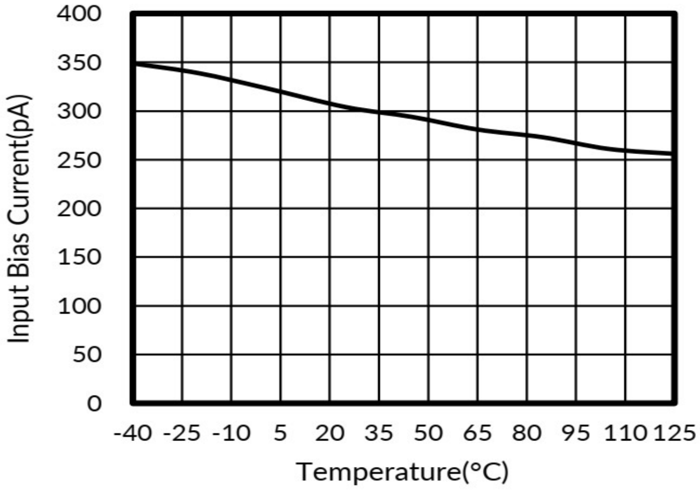


Figure 3. Input Bias Current vs Temperature

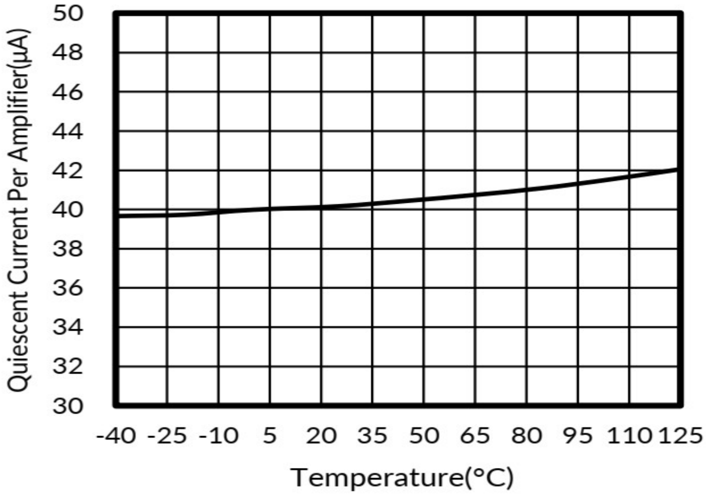


Figure 4. Quiescent Current vs Temperature

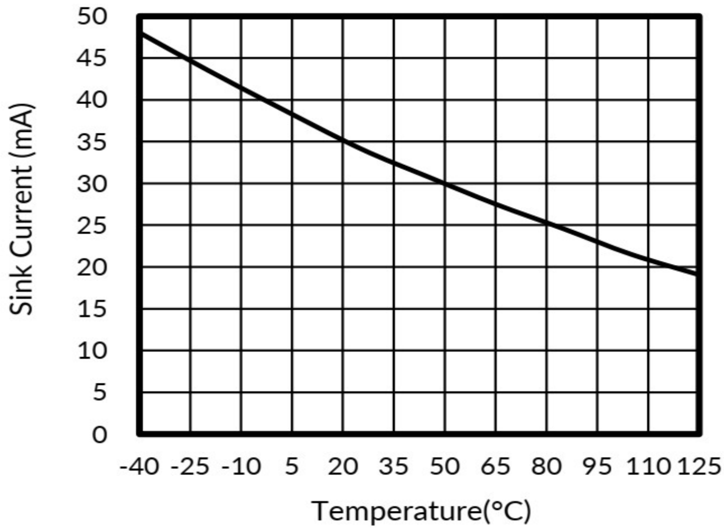


Figure 5. Sink Current vs Temperature

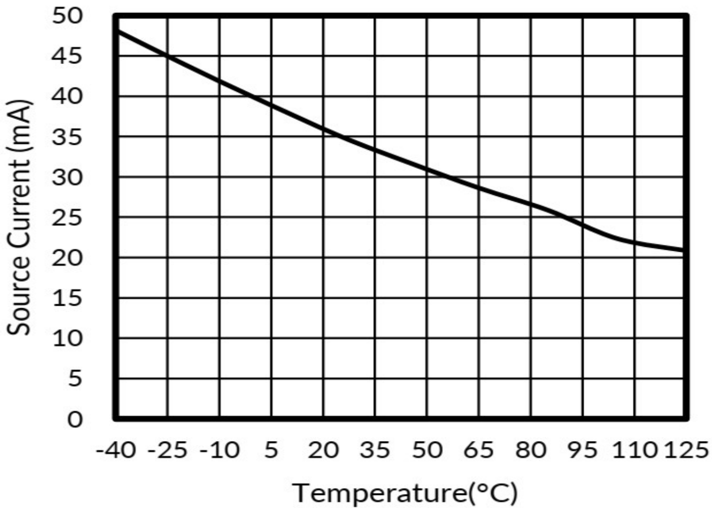


Figure 6. Source Current vs Temperature

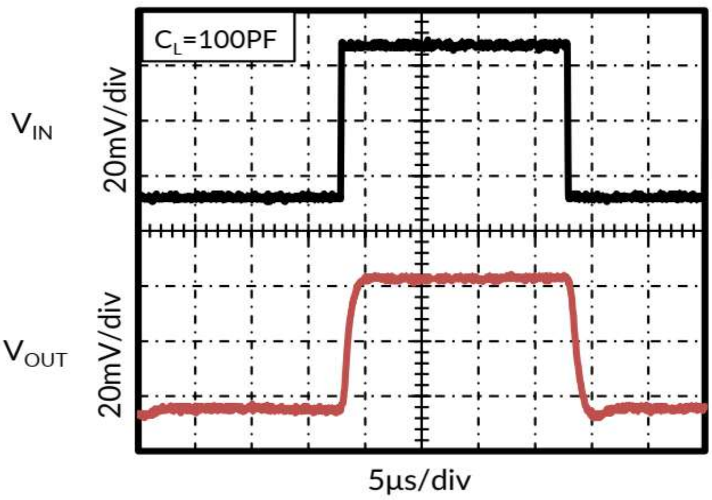


Figure 7. Small-Signal Step Response

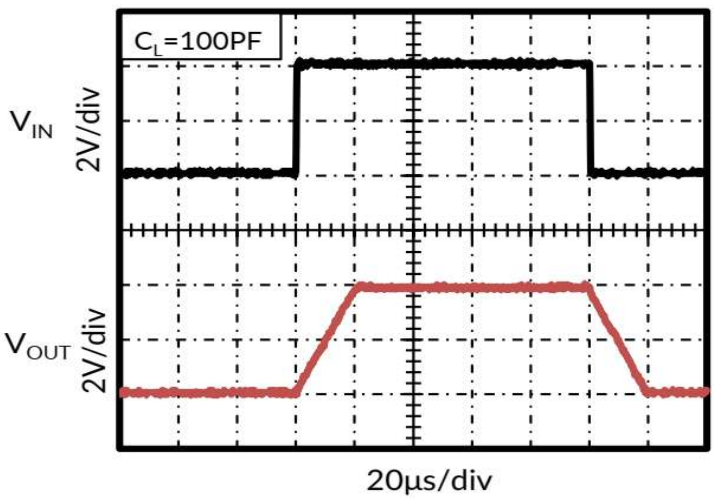


Figure 8. Large-Signal Step Response

Typical Performance Characteristics(Con.)

(TA = +25°C, VS=5V, RL = 10kΩ connected to VS/2, VOUT = VS/2, unless otherwise noted.)

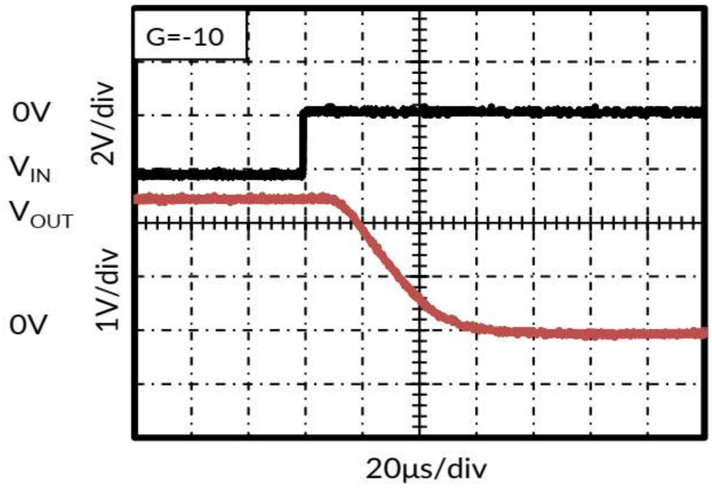


Figure 9. Positive Overvoltage Recovery

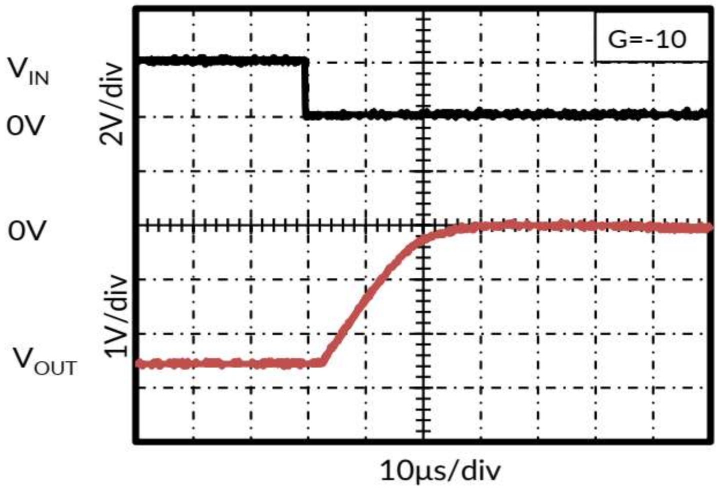


Figure 10. Negative Overvoltage Recovery

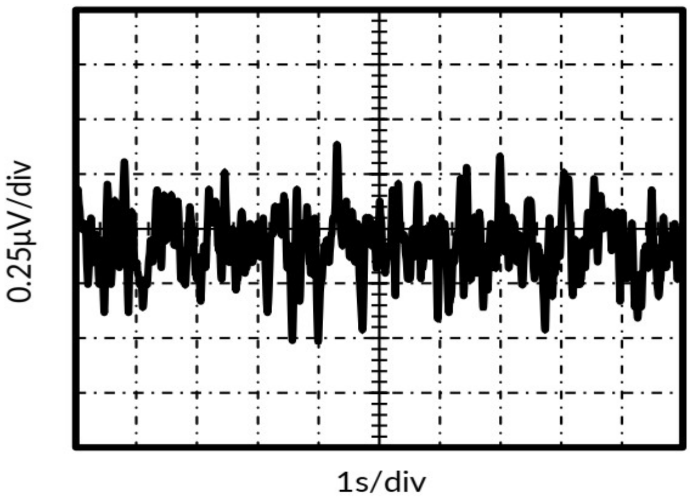


Figure 11. 0.1Hz to 10Hz Noise

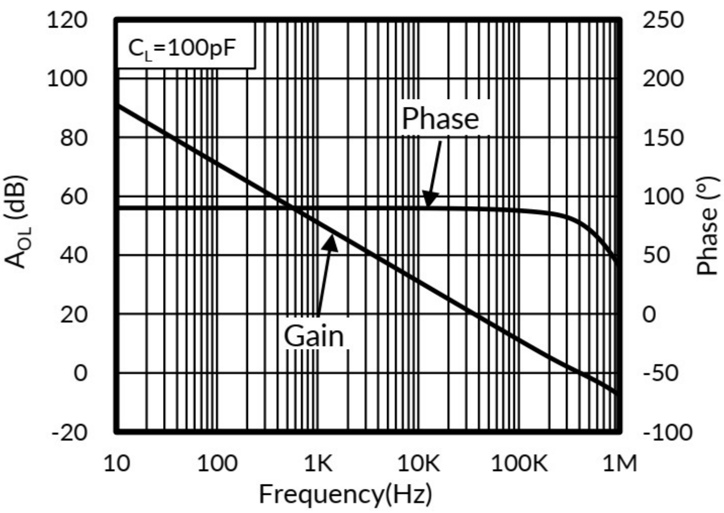


Figure 12. Open-Loop Gain and Phase vs Frequency

Feature Description

The HCR8541/HCR8542 series op amps are unity-gain stable and free from unexpected output phase reversal. They use auto-zeroing techniques to provide low offset voltage and very low drift over time and temperature. Good layout practice mandates use of a 0.1μF capacitor capacitor placed closely across the supply pins.

For lowest offset voltage and precision performance, circuit layout and mechanical conditions should be optimized. Avoid temperature gradients that create thermoelectric (Seebeck) effects in thermocouple junctions formed from connecting dissimilar conductors. These thermally-generated potentials can be made to cancel by assuring that they are equal on both input terminals.

- Use low thermoelectric-coefficient connections (avoid dissimilar metals).
- Thermally isolate components from power supplies or other heat-sources.
- Shield op amp and input circuitry from air currents, such as cooling fans.

Following these guidelines will reduce the likelihood of junctions being at different temperatures, which can cause thermoelectric voltages of 0.1μV/°C or higher, depending on materials used.

Operating Voltage

The HCR8541/HCR8542 series op amps operate over a power-supply range of +2.0V to +5.5V (±1.0V to ±2.75V), Supply voltages higher than 7V (absolute maximum) can permanently damage the amplifier. Parameters that vary over supply voltage or temperature are shown in the Typical Characteristics section of this data sheet

Typical Applications

Bidirectional Current-Sensing

This single-supply, low-side, bidirectional current-sensing solution detects load currents from -1A to 1A. The single '-ended output spans from 110mV to 3.19V. This design uses the HCR8541/HCR8542 because of its low offset voltage and rail-to-rail input and output. One of the amplifiers is configured as a difference amplifier and the other provides the reference voltage.

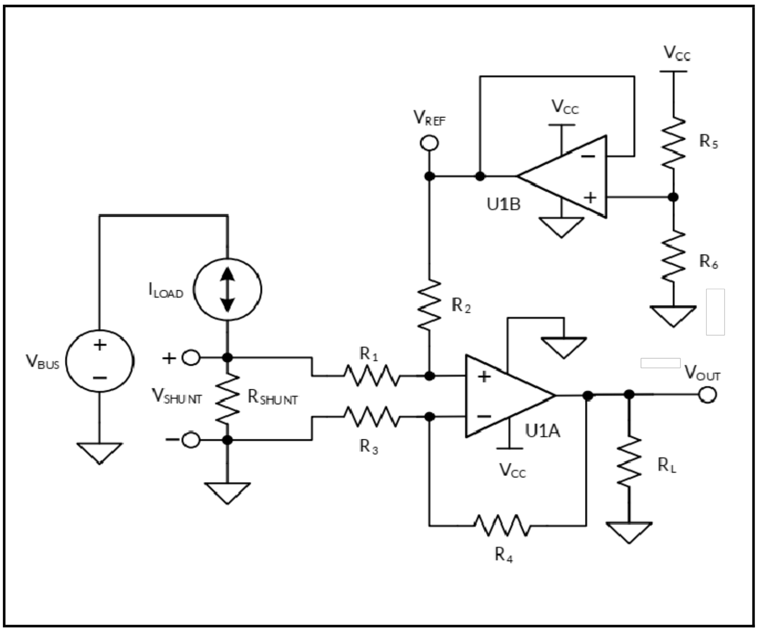


Figure 13. Bidirectional Current-Sensing Schematic

Design Requirements

This solution has the following requirements:

- Supply voltage: 3.3V
- Input: -1 A to 1 A
- Output: 1.65V ±1.54V (110mV to 3.19V)

Detailed Design Procedure

The load current, I_{LOAD}, flows through the shunt resistor (R_{SHUNT}) to develop the shunt voltage, V_{SHUNT}. The shunt voltage is then amplified by the difference amplifier which consists of U1A and R1 through R4. The gain of the difference amplifier is set by the ratio of R4 to R3.

Typical Applications(con.)

Detailed Design Procedure(con.)

To minimize errors, set R2 = R4 and R1 = R3. The reference voltage, VREF, is supplied by buffering a resistor divider using U1B. The transfer function is given by Equation 1.

$V_{OUT}=V_{SHUNT}\times Gain_{Diff\_Amp}+V_{REF}$

Where

$V_{SHUNT}=I_{LOAD}\times R_{SHUNT}$

$Gain_{Diff\_Amp} = R4/R3$

$V_{REF} = V_{CC} \times [R6/(R5+R6)]$ (1)

There are two types of errors in this design: offset and gain. Gain errors are introduced by the tolerance of the shunt resistor and the ratios of R4 to R3 and, similarly, R2 to R1. Offset errors are introduced by the voltage divider(R5 and R6) and how closely the ratio of R4/R3 matches R2/R1. The latter value impacts the CMRR of the difference amplifier, which ultimately translates to an offset error. Because this is a low-side measurement, the value of VSHUNT is the ground potential for the system load. Therefore, it is important to place a maximum value on VSHUNT. In this design, the maximum value for VSHUNT is set to 100 mV. Equation 2 calculates the maximum value of the shunt resistor given a maximum shunt voltage of 100 mV and maximum load current of 1 A

$$R_{SHUNT(Max)}=\frac{V_{SHUNT(Max)}}{I_{LOAD(Max)}}=\frac{100\ mV}{1\ A}=100\ m\Omega \quad (2)$$

The tolerance of RSHUNT is directly proportional to cost. For this design, a shunt resistor with a tolerance of 0.5% was selected. If greater accuracy is required, select a 0.1% resistor or better.

The load current is bidirectional; therefore, the shunt voltage range is –100 mV to 100 mV. This voltage is divided down by R1 and R2 before reaching the operational amplifier, U1A. Take care to ensure that the voltage present at the noninverting node of U1A is within the common-mode range of the device. Therefore, it is important to use an operational amplifier, such as the HCR8541 and HCR8542 that has a common-mode range that extends below the negative supply voltage. Finally, to minimize offset error, note that the HCR8541, HCR8542 has a typical offset voltage of ±3μV (±30μV maximum). Given a symmetric load current of -1A to 1A, the voltage divider resistors (R5 and R6) must be equal. To be consistent with the shunt resistor, a tolerance of 0.5% was selected. To minimize power consumption, 10kΩ resistors were used. To set the gain of the difference amplifier, the common-mode range and output swing of the HCR8541/HCR8542 must be considered. Equation 3 and Equation 4 depict the typical common-mode range and maximum output swing, respectively of the HCR8541, and HCR8542 given a 3.3V supply.

$$-100mV < V_{CM} < 3.4V \quad (3)$$

$$100mV < V_{OUT} < 3.2V \quad (4)$$

The gain of the difference amplifier can now be calculated as shown in Equation 5.

$$Gain_{Diff\_Amp}=\frac{V_{OUT\_Max}-V_{OUT\_Min}}{R_{SHUNT}\times(I_{MAX}-I_{MIN})}=\frac{3.2\ V-100\ mV}{100\ m\Omega\times[1\ A-(-1A)]}=15.5\ \frac{V}{V}$$

The resistor value selected for R1 and R3 was 1kΩ. 15.4kΩ was selected for R2 and R4 because it is the nearest standard value. Therefore, the ideal gain of the difference amplifier is 15.4V/V

The gain error of the circuit primarily depends on R1 through R4. As a result of this dependence, 0.1% resistors were selected. This configuration reduces the likelihood that the design requires a two-point calibration. A simple one-point calibration, if desired, removes the offset errors introduced by the 0.5% resistors.

Detailed Design Procedure(Con.)

Application Curve

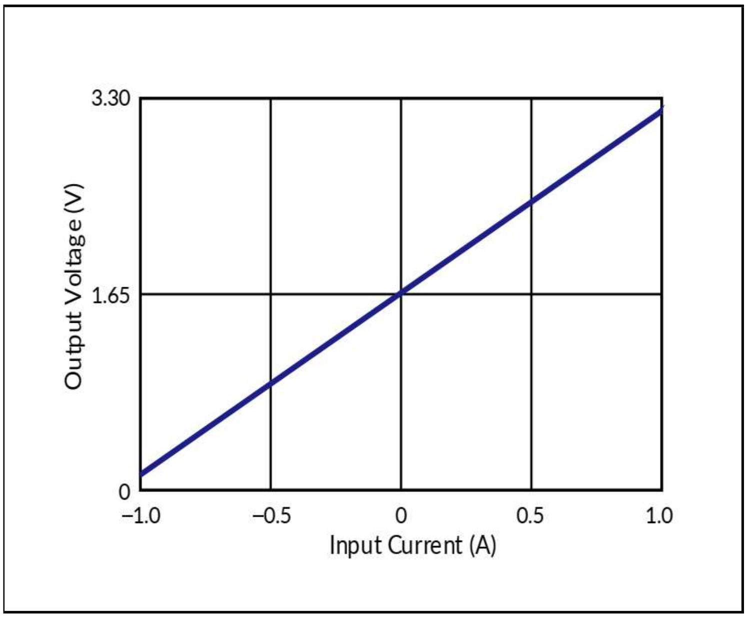


Figure 14. Bidirectional Current-Sensing Circuit Performance: Output Voltage vs Input Current

Layout Guidelines

Attention to good layout practices is always recommend Keep traces short. When possible, use a PCB ground plane with surface-mount components placed as close to the device pins as possible. Place a 0.1uF capacitor closely across the supply pins.

These guidelines should be applied throughout the analog circuit to improve performance and provide benefits such as reducing the EMI susceptibility.

Layout Example

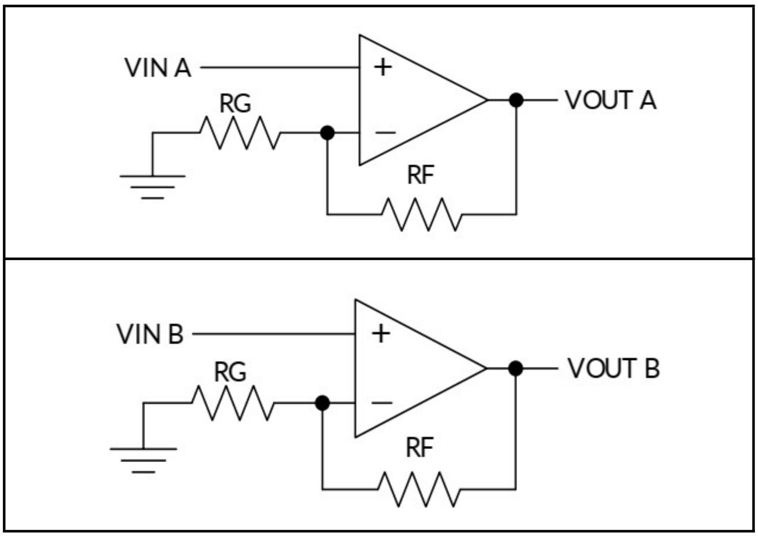
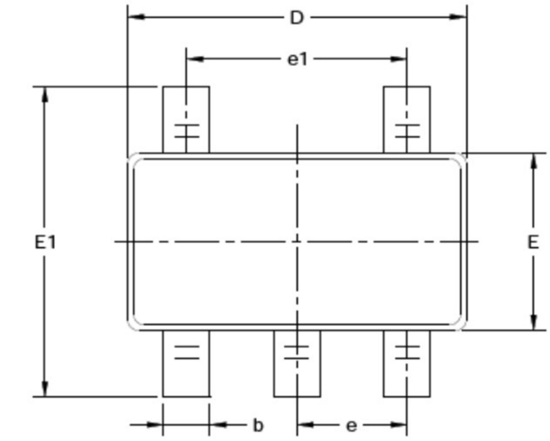
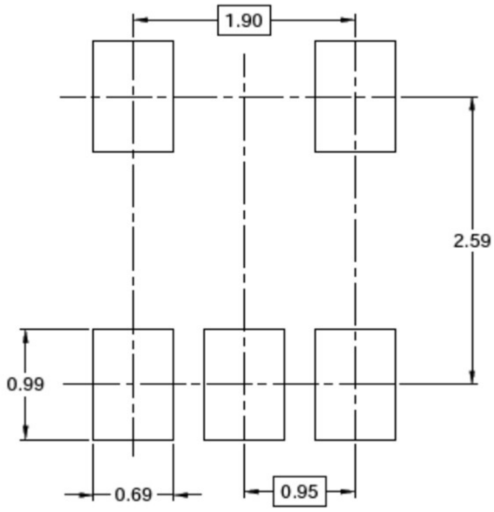


Figure 15. Schematic Representation

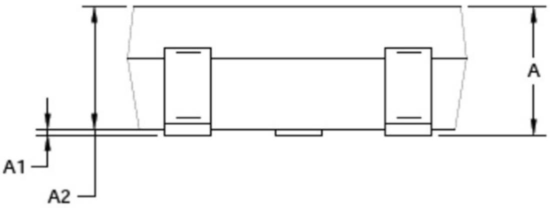
Mechanical Dimensions

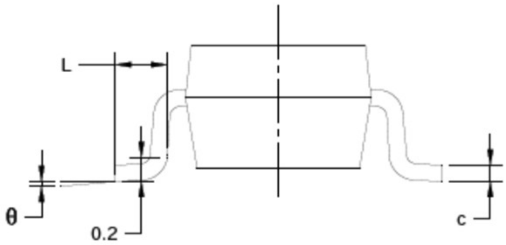
M5: SOT23-5 package





RECOMMENDED LAND PATTERN (Unit: mm)



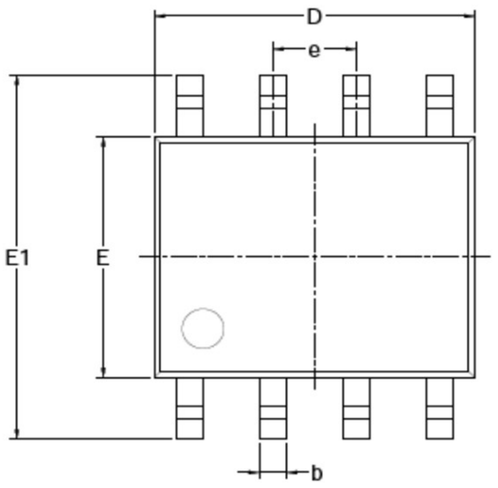


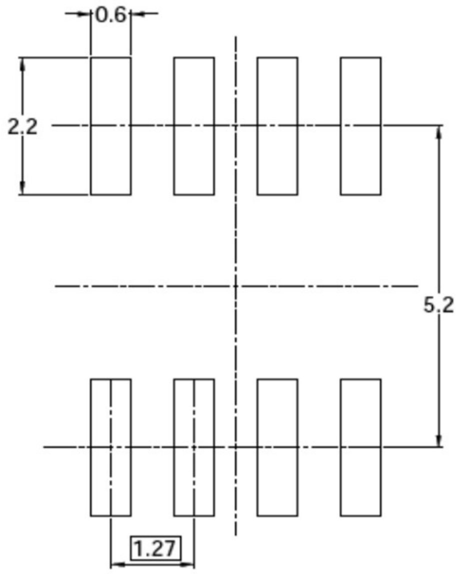
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950 BSC		0.037 BSC	
e1	1.900 BSC		0.075 BSC	
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

NOTES:
1. Body dimensions do not include mode flash or protrusion.
2. This drawing is subject to change without notice.

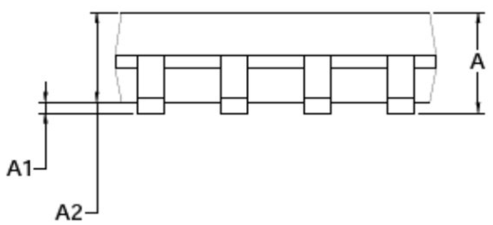
Mechanical Dimensions(Con.)

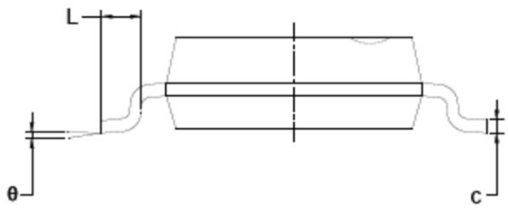
M8: SOIC-8(SOP-8) Package





RECOMMENDED LAND PATTERN (Unit: mm)

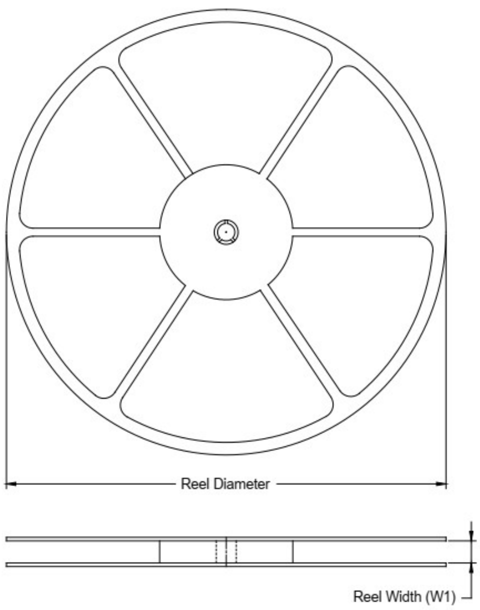


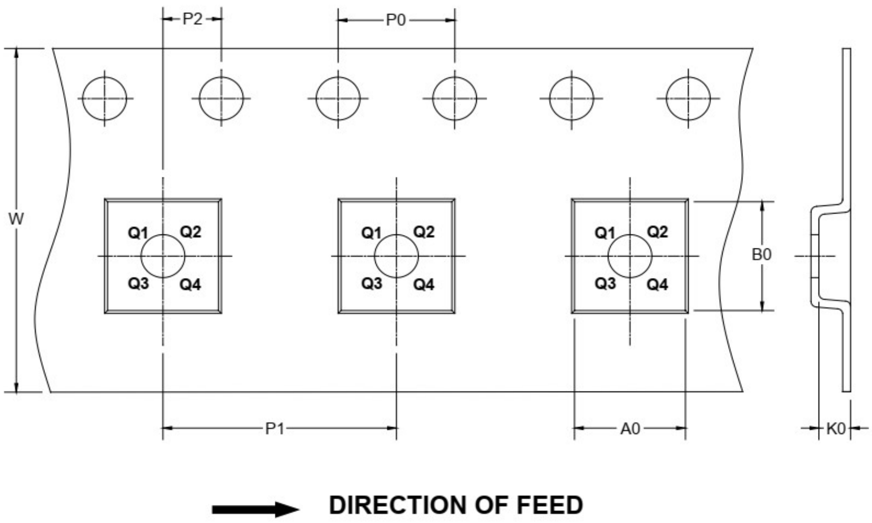


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.27 BSC		0.050 BSC	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

NOTES:
1. Body dimensions do not include mode flash or protrusion.
2. This drawing is subject to change without notice.

Tape and Reel Information





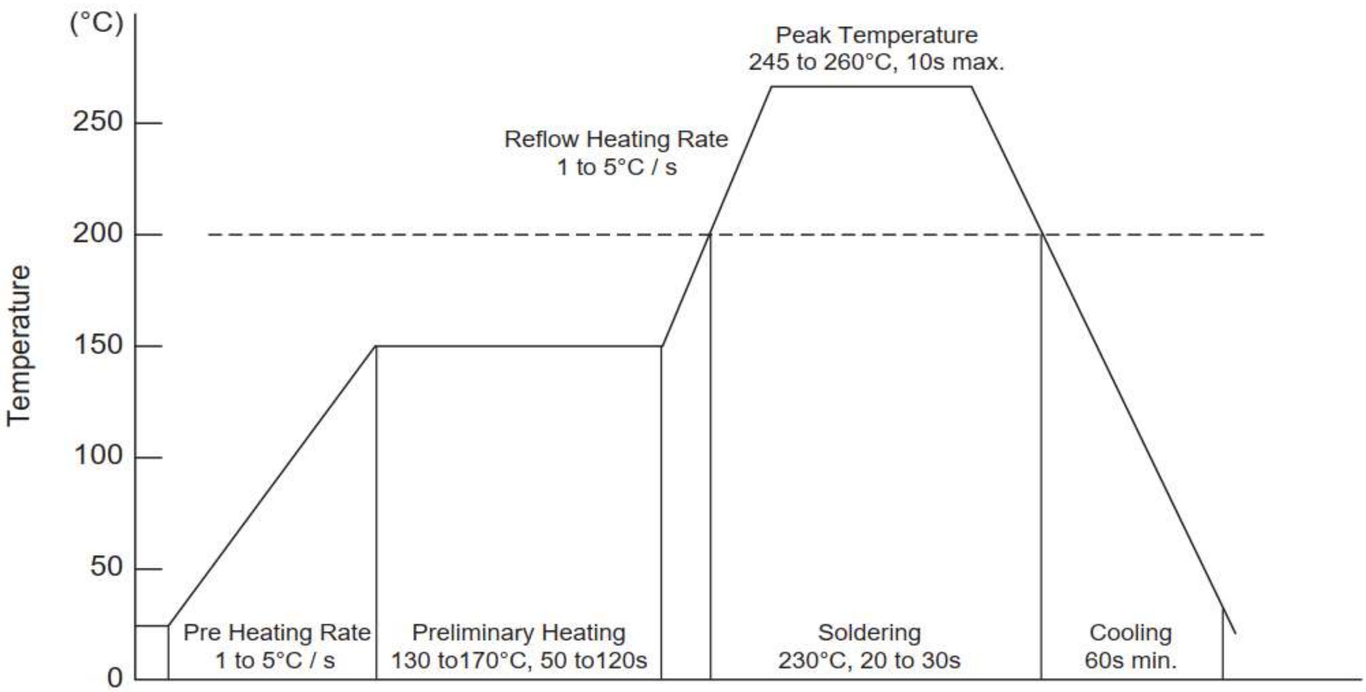
NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF TAPE AND REEL

Package Type	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
SOT-23-5	7"	9.5	3.20	3.20	1.40	4.0	4.0	2.0	8.0	Q3
SOIC-8	13"	12.4	6.40	5.40	2.10	4.0	8.0	2.0	12.0	Q1

Conditins of Soldering and Storage

* Recommended condition of reflow soldering



Recommended peak temperature is over 245'C, if peak temperature is below 245'C, you may adjust the following parameters:

* Time length of peak temperature (longer)
* Time length of soldering (longer)
* Thickness of solder paste (thicker)

* Conditions of hand soldering
  * Temperature : 300'C
  * Time : 3s max
  * Times : one time

* Storage conditions
  * Temperature
    5 to 40'C
  * Humidity
    30 to 80% RH
  * Recommended period
    One year after manufacturing